RJK6054DPP-M0

Silicon N Channel MOS FET
High Speed Power Switching

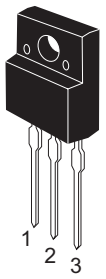
REJ03G1801-0100
Rev.1.00
Jul 02, 2009

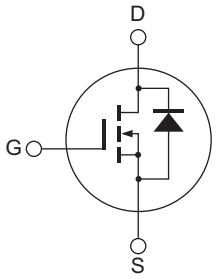
Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline

RENESAS Package code: PRSS0003AF-A)
(Package name: TO-220FL)





1. Gate
2. Drain
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	600	V
Gate to source voltage	V_{GSS}	±30	V
Drain current	I_D Note4	16	A
Drain peak current	$I_{D\ (pulse)}$ Note1	32	A
Body-drain diode reverse drain current	I_{DR}	16	A
Body-drain diode reverse drain peak current	$I_{DR\ (pulse)}$ Note1	32	A
Avalanche current	I_{AP} Note3	4	A
Avalanche energy	E_{AR} Note3	0.87	mJ
Channel dissipation	Pch Note2	35	W
Channel to case thermal impedance	θch-c	3.57	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Notes: 1. PW ≤ 10 µs, duty cycle ≤ 1%
2. Value at Tc = 25°C
3. STch = 25°C, Tch ≤ 150°C
4. Limited by maximum safe operation area

Electrical Characteristics

(Ta = 25°C)

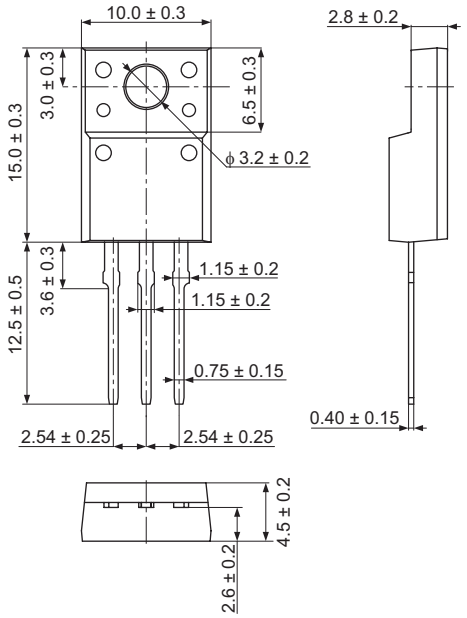
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	—	—	V	I_D = 10 mA, V_{GS} = 0
Zero gate voltage drain current	I_{DSS}	—	—	1	µA	V_{DS} = 600 V, V_{GS} = 0
Gate to source leak current	I_{GSS}	—	—	±0.1	µA	V_{GS} = ±30 V, V_{DS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	—	4.5	V	V_{DS} = 10 V, I_D = 1 mA
Static drain to source on state resistance	$R_{DS(on)}$	—	0.475	0.720	Ω	I_D = 8 A, V_{GS} = 10 V Note5
Input capacitance	Ciss	—	1730	—	pF	V_{DS} = 25 V V_{GS} = 0 f = 1 MHz
Output capacitance	Coss	—	175	—	pF	
Reverse transfer capacitance	Crss	—	21	—	pF	
Turn-on delay time	$t_{d(on)}$	—	35	—	ns	I_D = 8 A V_{GS} = 10 V R_L = 37.5 Ω Rg = 10 Ω
Rise time	t_r	—	22	—	ns	
Turn-off delay time	$t_{d(off)}$	—	88	—	ns	
Fall time	t_f	—	18	—	ns	
Total gate charge	Qg	—	45	—	nC	V_{DD} = 480 V V_{GS} = 10 V I_D = 16 A
Gate to source charge	Qgs	—	8.7	—	nC	
Gate to drain charge	Qgd	—	20.8	—	nC	
Body-drain diode forward voltage	V_{DF}	—	0.91	1.50	V	I_F = 16 A, V_{GS} = 0 Note5
Body-drain diode reverse recovery time	t_{rr}	—	330	—	ns	I_F = 16 A, V_{GS} = 0 di_F/dt = 100 A/µs

Notes: 5. Pulse test

Package Dimension

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
TO-220FL	—	PRSS0003AF-A	TO-220FL	1.5g

Unit: mm



Ordering Information

Part No.	Quantity	Shipping Container
RJK6054DPP-M0-T2	1050 pcs	Box (Tube)

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RENESAS SALES OFFICES

http://www.renesas.com

Refer to "**http://www.renesas.com/en/network**" for the latest and detailed information.

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